EDTM2020 - Preliminary Advance Program

As of January 29, 2020

Day 2 - Tuesday, March 17 Or30-08:30 Room C (Grand Ballroom I) Women in Engineering / Young Professional Event 0330-16:00 Main Room (Matahari I, II, III) Plenary Session 2 Chair samar Suba 30 9.15 PL-4 Critical Feature Size of Device Manufacturing for Dominating MOSFET Evolutions Digh Hisamoto Htachi, Ltd. 315 10.00 PL-5 Resarch Toward Monolithic Three-Dimensional Ics Lance Li Taiwan Semiconductor Manufacturing Company (TSMC) 0000-10:15 Main Room (Matahari I, II, III) Social Kathari I, III, III) Social Kathari I, III, III) Store Break Main Room (Matahari I, II, III) Excuss Session 4M Focus Session 2: Reliability and DTCO Chairs: Social Kathari I, II, III) Decice Retrinking Reliability for Net Generation Electronic Muhammad A Alam Pardue University, West Lafayette 10:40 4M-1 Invited Anded for Hole Trapping-Detrapping Kinetcs During NBTI in p-Channel FETs Social Kathapara Indian Institute of Technology Bombay 11:55 11:30 4M-3 Invited Reliability of Advanced FinFET Technology Nodes Bayon Planar Hyun Chai Sagong Fourdry Business, Samang Electronics
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As of January 29, 2020

Day 2	- Tuesd	lay, Ma	arch 17			·
13:20-15				Room C (Grand Ballroom I)		
Session Chairs:	SC Roger B	ooth, Ch	en Jiang	Sensors and Inductors		
13:20	13:45	5C-1	Invited	Integration of Gas Sensors with CMOS Technology	Siegfried Selberherr	Institute for Microelectronics, TU Wien
13:45	14:10	5C-2		High Performance and Wireless Graphene Earphone Towards Practical Applications	Yuhong Wei	Tsinghua University
14:10	14:35	5C-3		CMOS Low Power Current Source Based Tunable Inductor for IoT Devices	Selvakumar Mariappan	Universiti Sains Malaysia
4:35	15:00	5C-4	Invited	Overview of Recent Advances in Flexible Highly Compliant Magnetoelectronics	Denys Makarov	Institute of Ion Beam Physics and
15:00-15				Authors' Interview / Poster Viewing / Coffee Break		Materials Research
13:20-15				Room D (Grand Ballroom III)		
Session		D-:	14/ 1 :	Materials for Manufacturing		
2 hairs: 3:20	Asrul Ni 13:45	5D-1	-vven Li	Patterning Platinum by Selective Wet Etching of Sacrificial Pt-Al Alloy	Sebastian Meier	Texas Instruments Incorporated &
3:45	14:10	5D-2		Carbon Nanotubes to Enable Advanced Lithography	Marina Y. Timmermans	Technische Universitaet Muenchen imec
			المع بأخله ما	Printed Graphene Aerosol Gel Micro-Supercapacitors: Towards Flexible Energy		
4:10	14:35	5D-3	Invited	Storage Devices SnO Thin Films Prepared by Reactive Sputtering for Ambipolar Thin-Film Transistor	Suprem Das	Kansas State University
4:35	15:00	5D-4		Applications	Jingyong Huo	Fudan University
5:00-15				Authors' Interview / Poster Viewing / Coffee Break		
15:20-17 Session				Room A (Matahari I) Reliability 2		
Chairs:	Norhaya	ati Binti S	Soin, Du	rga Misra	T	
5:20	15:45	6A-1		Impact and Quantization of Short-Term Relaxation Effect in Analog RRAM	Yue Xi	Tsinghua University
5:45	16:10	6A-2		Reliability of 2DEG Diamond FET by Harsh-Continuous Stress Voltage Approach	Mohd Syamsul	Institute of Nano Optoelectronics Research and Technology (INOR), USM
6:10	16:35	6A-3		Analysis and Failure Modes of Highly Degraded PV Modules Inspected During the 2018 All India Survey of PV Module Reliability	Juzer Vasi	IIT Bombay
6:35	17:00	6A-4		Hydrogen Proton Induced HTRB Reliability Degradation	David Goh	STMicroelectronics Asia Pacific Pte Ltd
17:00-17	7:15			Authors' Interview		
15:20-17 Session				Room B (Matahari III) Memory Modeling and Interface Trap Modeling		
Chairs:	Dondee	Navarro	, Takesh			
5:20	15:45	6B-1		Perpendicular STT-MRAM Switching at Fixed Voltage and at Fixed Current	Simone Fiorentini	CDL NOVOMEMLOG, Institute for Microelectronics, TU Wien
				Extraction of Mobility in 3-D NAND Flash Memory with Poly-Si Based Macaroni	Hyungjun Jo	
5:45	16:10	6B-2		Structure	. I yangjan se	Seoul National University
	16:10 16:35	6B-2 6B-3		Structure Improved Lumped Element Model for GaN-based MIS-HEMT Gate Stack in the Spill-Over Regime	Narendra Suresh Rai	
6:10				Improved Lumped Element Model for GaN-based MIS-HEMT Gate Stack in the Spill-Over Regime Impact of Interface Traps and Zn Diffusion on Performance of Lateral Hybrid III-V/Si	Narendra Suresh Rai	
15:45 16:10 16:35 17:00-17	16:35 17:00	6B-3		Improved Lumped Element Model for GaN-based MIS-HEMT Gate Stack in the Spill-Over Regime	Narendra Suresh Rai	Indian Institute of Technology Bombay
6:10 6:35 7:00-17 5:20-17	16:35 17:00 7:15 7:00	6B-3		Improved Lumped Element Model for GaN-based MIS-HEMT Gate Stack in the Spill-Over Regime Impact of Interface Traps and Zn Diffusion on Performance of Lateral Hybrid III-V/Si Photodetectors Authors' Interview Room C (Grand Ballroom I)	Narendra Suresh Rai	Indian Institute of Technology Bombay
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